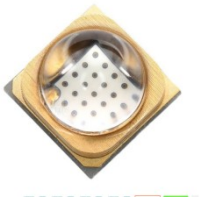
HK365S35CL-S45



Specification Datasheet

CFCL Optoelectronics (Shenzhen) Co., Ltd.

Model No.: HK365S35CL-S45

Product: 3535 Round Lens Package UVA LED (45*45mil Chip)

Revision: V1.1

Date: November 2026

Table of Contents

No.	Item	Page
1	General Description	2
2	Key Features	2
3	Application Fields	2
4	Absolute Maximum Ratings	3
5	Electro-Optical Characteristics	3
6	Binning Specifications	4
7	Outline Dimensions	4
8	Characteristic Curve	5
9	Packaging & Storage	5
10	Notes & Precautions	6

1. General Description

This is a high-photon-energy shortwave UVA solid-state light source optimized for 500mA continuous operation, with a typical peak wavelength of 365 nm. It adopts a standard 3535 SMD package with a high-purity aluminum nitride (AIN) ceramic substrate and a 60° spherical fused silica lens, delivering concentrated high-irradiance output with strong photochemical activity.

The AIN substrate provides ultra-low thermal resistance, ensuring stable radiant power and long service life under continuous operation. This wavelength band is optimized for high-precision photochemical and analytical applications requiring short-wavelength high-energy UV excitation.

2. Key Features

- Peak wavelength: typical 365.0 nm, full binning range 365.0 – 375.0 nm (shortwave UVA band)
- 3535 SMD aluminum nitride (AIN) ceramic package, thermal conductivity ≥ 170 W/m·K
- 60° half-intensity beam angle with high-purity fused silica spherical lens
- High photon energy for efficient photochemical activation and fluorescence excitation
- Low thermal resistance and excellent heat dissipation for long-term stable output
- Low luminous degradation under continuous high-current driving
- 100% electrical and optical inspection before shipment
- RoHS, CE and REACH compliant

3. Application Fields

- High-precision photolithography and micro-fabrication processes
- High-sensitivity fluorescence detection and biochemical immunoassay instruments
- Specialty UV curing of high-energy photoresists, precision adhesives and functional coatings
- Industrial non-destructive testing (NDT) and fluorescent penetrant inspection
- Photochemical synthesis and laboratory photobiology research
- High-grade counterfeit verification and forensic trace detection
- Semiconductor wafer processing and mask exposure

4. Absolute Maximum Ratings

(Test condition: Ambient temperature Ta = 25°C)

Parameter	Symbol	Rating	Unit
Forward Current	I_F	700	mA
Peak Forward Current (10% duty cycle, 1ms pulse)	$I_{F(peak)}$	⩽1500	mA
Reverse Voltage	V_R	5.0	V
Operating Temperature Range	T_{opr}	-40 ~ +85	°C
Storage Temperature Range	T_{stg}	-40 ~ +100	°C
Maximum Junction Temperature	T_j	105	°C

5. Electro-Optical Characteristics

(Test condition: Ta = 25°C, Forward current I_F = 500 mA)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Peak Wavelength	λ_p	365.0	368.0	375.0	nm
Spectral Half-Width	Δλ	-	13	-	nm
Forward Voltage	V_F	3.4	-	3.8	V
Radiant Output Power	P_e	860.0	980.0	1100.0	mW
Viewing Angle (Half Intensity)	$2\theta_{1/2}$	-	60	-	deg
Reverse Leakage Current	I_R	-	-	1.0	μA
Thermal Resistance (Junction to Board)	$R_{th(j-b)}$	-	12	15	°C/W

6. Binning Specifications

(Test condition: Ta = 25°C, I_F = 500 mA)

6.1 Forward Voltage Binning

Level	A01	A02	A03	A04
Min. (V)	3.4	3.5	3.6	3.7
Max. (V)	3.5	3.6	3.7	3.8

6.2 Radiometric Power Binning

Level	S45-86	S45-90	S45-94	S45-98	S45-102	S45-106
Min.(mW)	860.0	900.0	940.0	980.0	1020.0	1060.0
Max.(mW)	900.0	940.0	980.0	1020.0	1060.0	1100.0

6.3 Dominant Wavelength Binning

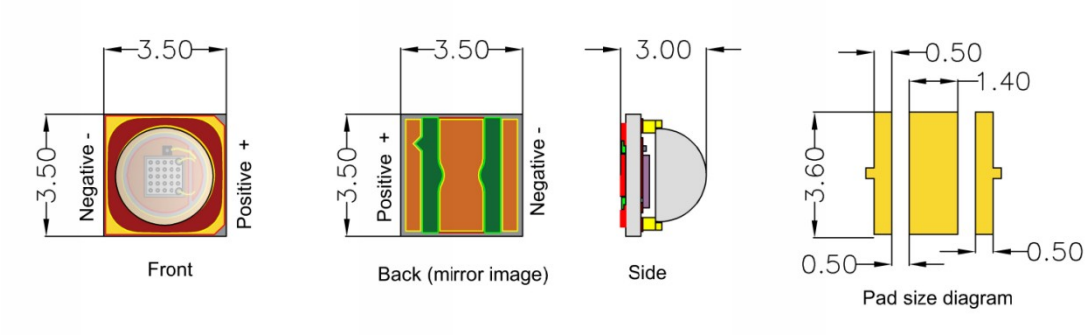
Level	365B	370A
Min.	365.0 nm	370.0 nm
Max.	370.0 nm	375.0 nm

Default supply: 365B bin; 370A bin available upon custom request.

7. Outline Dimensions

- **Package Type:** 3535 SMD Round Lens
- **Overall Dimensions:** 3.50 ± 0.10 mm (Length) × 3.50 ± 0.10 mm (Width) × 3.00 ± 0.10 mm (Height)
- **Lens Diameter:** φ2.8mm (High-purity quartz glass)
- **Pad Layout:** Standard 3535 SMD footprint

- **Polarity Marking:** Anode (+) and Cathode (-) marked on the back of the package (mirror view)
- **Pad Size:** Symmetrical pad design compatible with standard 3535 SMD reflow soldering processes



8. Characteristic Curve

Fig.1-Relative Luminous Intensity vs. Forward Current

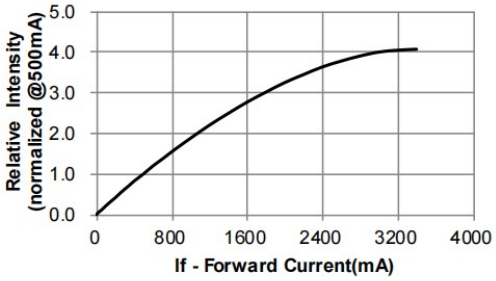


Fig.2-Forward Current vs. Forward Voltage

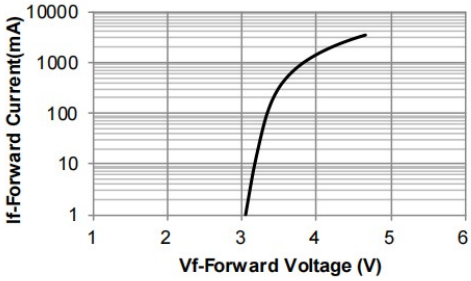


Fig.3-Relative Intensity (@500mA) vs. Ambient Temperature

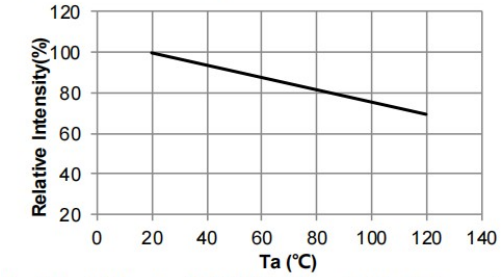


Fig.4-Forward Voltage (@500mA) vs. Ambient Temperature

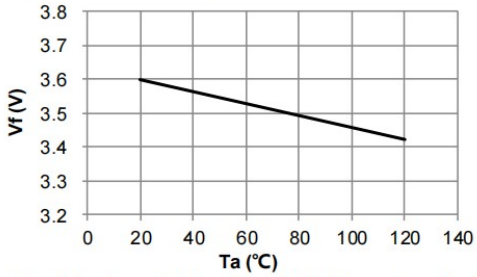


Fig.5- Peak Wavelength (@500mA) vs. Ambient Temperature

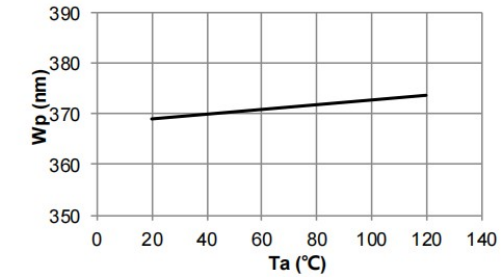
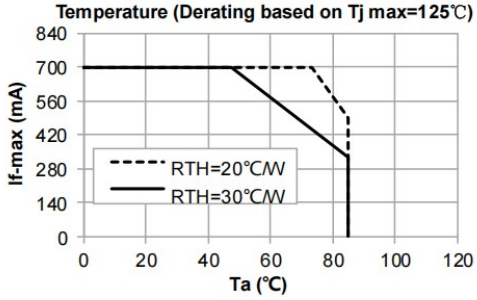


Fig.6-Maximum Driving Forward DC Current vs. Ambient Temperature (Derating based on Tj max=125℃)



9. Packaging & Storage

9.1 Packaging

- Packaging form: Tape and reel
- Quantity per reel: 600 pieces
- Reel diameter: 178 mm (7 inch)
- Moisture Sensitivity Level: MSL 3

9.2 Storage Conditions

- Store in a dry environment at room temperature
- Recommended storage: 5°C ~ 30°C, 30% ~ 70% RH
- Avoid direct sunlight, corrosive gases and high humidity
- Reseal the moisture barrier bag properly after opening
- For MSL 3 devices, complete soldering within 168 hours after opening the bag under factory environment (≤ 30°C / 60% RH); bake before use if expired.

10. Notes & Precautions

- Peak wavelength measurement tolerance: ± 2.0 nm
- Radiant power measurement tolerance: ± 10%
- Forward voltage measurement tolerance: ± 10%
- All parameters are tested on finished devices under standard conditions (\(T_a=25^\circ C\), \(I_F=500mA\)) via integrating sphere system.
- UVA LEDs emit high-energy ultraviolet radiation. Avoid direct exposure to eyes or skin during operation.
- This device is sensitive to electrostatic discharge (ESD). ESD withstand voltage: HBM ± 2000 V. Proper ESD protection is required during handling and assembly.
- Operating beyond absolute maximum ratings may cause permanent damage to the device.
- Proper thermal design is required to ensure junction temperature does not exceed 105°C under continuous operation.
- Chip-level maximum ratings (S-45BUPUT-A): DC forward current ≤ 700 mA, junction temperature ≤ 125°C. The package-level limits stated in Section 4 govern continuous operation of this device.